



# N-Channel 650 V (D-S) Super Junction MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}$ ( $\Omega$ ) TYP.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
650	0.173 at V <sub>GS</sub> = 10 V	20	18		

### **FEATURES**

- Super Junction MOSFET
- 100 % R<sub>g</sub> and UIS Tested
- Easy to use/drive





- Computing
  - PC silver box / ATX power supplies
- Lighting
  - Two stage LED lighting
- Consumer electronics
- Applications using hard switched topologies
  - Power factor correction (PFC)
  - Two switch forward converter
  - Flyback converter
- Switch mode power supplies (SMPS)

TO-252 Pin Configuration	G G
Top View	S N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
Parameter	Symbol	Limit	Unit			
Drain-Source Voltage	V <sub>DS</sub>	650	V			
Gate-Source Voltage	$V_{GS}$	± 30	V			
Continuous Drain Current	T <sub>C</sub> = 25 °C	L	20			
Continuous Diain Current	T <sub>C</sub> = 100 °C	I <sub>D</sub>	15	A		
Pulsed Drain Current (t = 300 μs)	I <sub>DM</sub>	72	A			
Avalanche Current	I <sub>AS</sub>	18.9				
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	57	mJ		
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	97 <sup>b</sup>	W		
iviaximum Fower Dissipation	T <sub>A</sub> = 25 °C°	T FD	2.1	VV		
Operating Junction and Storage Tempera	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150	°C			

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	65	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	2			

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#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Base on  $T_C$  = 25 °C.

Rev. 1.0



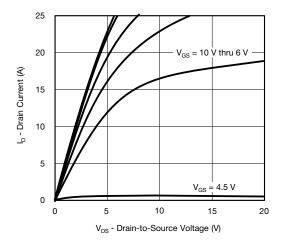
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	•			•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V, } I_D = 250  \mu\text{A}$				
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	4	4	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	S = 0 V, V <sub>GS</sub> = ± 20 V		± 100	nA
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate voltage Drain Gurrent	I <sub>DSS</sub>	V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	
		V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C			250	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α
Drain Course On State Besistance	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A,TJ= 25 °C		0.173	0.195	0
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 5 A,TJ= 150 °C		0.438		Ω
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 5 A		15		S
Dynamic <sup>b</sup>						
Input Capacitance	C <sub>iss</sub>			1010		
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, f = 1 MHz		25		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			11		
Total Gate Charge <sup>c</sup>	Qg			18		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 5 \text{ A}$		6.6		nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			8.1		
Gate Resistance	R <sub>g</sub>	f = 1 MHz	1 MHz 1.5			Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			8		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 400 \text{ V}, R_{L} = 9.6 \Omega$		11		ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 5.2 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 10\Omega$		18		115
Fall Time <sup>c</sup>	t <sub>f</sub>			5		
Drain-Source Body Diode Ratings ar	d Characteri	stics <sup>b</sup> T <sub>C</sub> = 25 °C				
Continuous Current	I <sub>S</sub>				20	۸
Pulsed Current	I <sub>SM</sub>				72	Α
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>F</sub> = 5 A, V <sub>GS</sub> = 0 V		0.9		V
Reverse Recovery Time	t <sub>rr</sub>			926		ns
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 5 A, dI/dt = 100 A/μs		22		Α
Reverse Recovery Charge	· · · · · ·			6		μC

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %. b. Guaranteed by design, not subject to production testing. c. Independent of operating temperature.

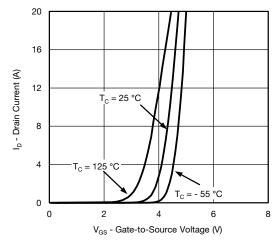
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



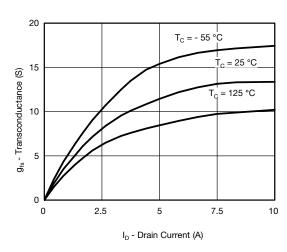
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



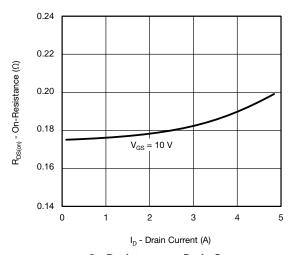
#### **Output Characteristics**



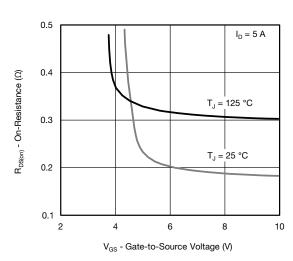
**Transfer Characteristics** 



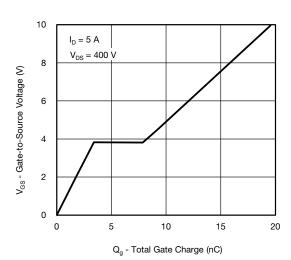
Transconductance



On-Resistance vs. Drain Current



On-Resistance vs. Gate-to-Source Voltage

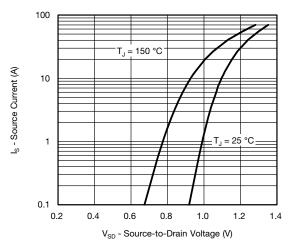


**Gate Charge** 

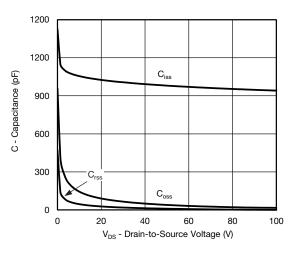




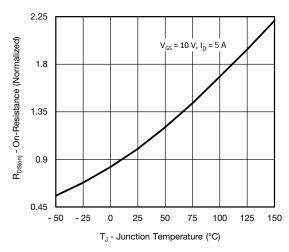
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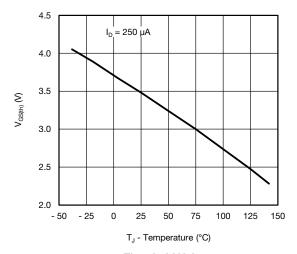
#### Source-Drain Diode Forward Voltage



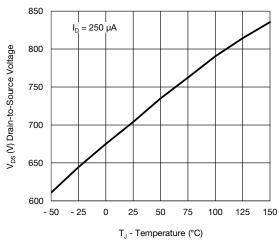
Capacitance



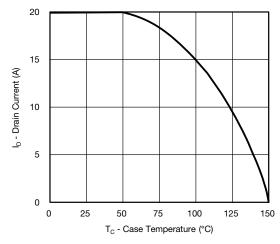
On-Resistance vs. Junction Temperature



Threshold Voltage



**Drain Source Breakdown vs. Junction Temperature** 

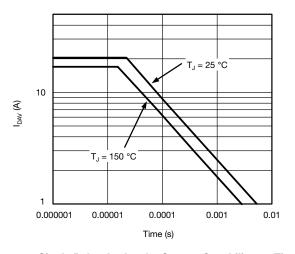


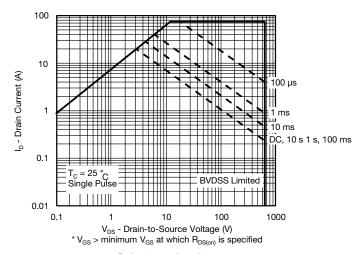
**Current Derating** 





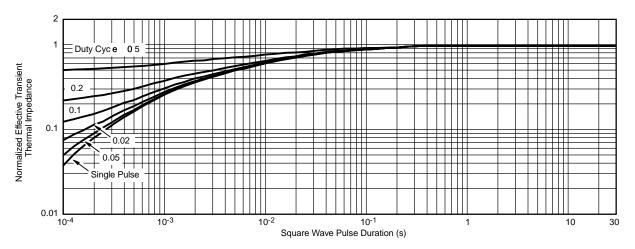
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Single Pulse Avalanche Current Capability vs. Time

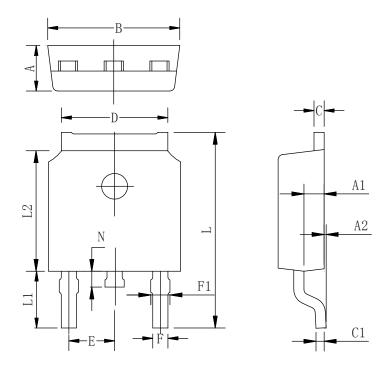




Normalized Thermal Transient Impedance, Junction-to-Case



# **TO-252-2L PACKAGE OUTLINE**



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
В	6.40	6.60	6.80
С	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
Е	2.286 TYP		
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
L	9.30	9.90	10.80
L1	2.4	2.8	3.6
L2	5.90	6.10	6.55
N	0.57	0.80	1.05





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